

6501130 NATL SEMICOND, (DISCRETE)

28C 35460 D

Type No.	Case Style	V <sub>CE0</sub> (V) Min	V <sub>CE0</sub> (V) Min	V <sub>EB0</sub> (V) Min	I <sub>CEX1</sub> (μA) Max	V <sub>CB</sub> (V)	I <sub>rFE</sub> Min	I <sub>rFE</sub> Max	I <sub>C</sub> (A) @	V <sub>CE(SAT)</sub> (V) Max	V <sub>BE(SAT)</sub> (V) Min & Max	I <sub>C</sub> (A) @	C <sub>ob1</sub> (pF) Max	f <sub>T</sub> (MHz) Min	I <sub>C</sub> (A) @	Process No.
MJE170	TO-126	40	40		0.1	60	12	1.7	1.5	1	1.7	3	50	50	0.1	77
MJE170	TO-126	40	40		100†	40	20	0.9	0.5	1	1.5	1.5				77
MJE171	TO-126	60	60		0.1	80	8	1.0	1.5	1	1.3	3				78
MJE171	TO-126	60	60		100†	80	20	0.4	0.5	1	1.5	1.5				78
MJE172	TO-126	80	80		0.1	100	12	1.7	1.5	1	2.0	3	50	50	0.1	79
MJE172	TO-126	80	80		100†	80	20	0.9	0.5	1	1.5	1.5				79
2N6489	TO-220	40	40		500†	45	8	1.0	1.5	1	1.3	5				5A
2N6490	TO-220	60	60		500†	65	20	1.3	5	4	5	15			1	5A
2N6491	TO-220	80	80		500†	85	5	1.3	15	4	5	5			1	5A
MJE2901T	TO-220	60	60				25	100	3	2		4				5A
MJE2955T	TO-220	60	60		1 mA	70	20	70	4	4	1.1	4				5A
TIP42	TO-220	40	40		400*	40	15	75	3	4	1.5	6			0.5	5A
TIP42A	TO-220	60	60		400*	60	30	75	3	4	1.5	6			0.5	5A
TIP42B	TO-220	80	80		400*	80	15	75	3	4	1.5	6			0.5	5A
TIP42C	TO-220	100	100		400*	100	15	75	3	4	1.5	6			0.5	5A

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6501130 NATL SEMICOND, (DISCRETE)

28C 35461 D

POWER (Continued)



Type No.	Case Style	V <sub>CE0</sub> (V) Min	V <sub>BE0</sub> (V) Min	V <sub>CB</sub> (V) Min	V <sub>CE</sub> (V) Min	V <sub>BE</sub> (V) Min	I <sub>CE0</sub> <sup>†</sup> (μA) Max	I <sub>CEX</sub> <sup>†</sup> (μA) Max	V <sub>CB</sub> (V) Min	I <sub>CE</sub> (A) Max	V <sub>CE</sub> (V) Min	I <sub>CE</sub> (A) Max	V <sub>BE(SAT)</sub> (V) Min	V <sub>CE(SAT)</sub> (V) Max	V <sub>BE(SAT)</sub> (V) Max	I <sub>CE(SAT)</sub> (A) Max	C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) Min	I <sub>C</sub> (A) Max	Process No.
2N6193	TO-126	40		40	4	2	100	4	4	2	0.6	1.5	1.2	1.2	1.2	1.5		2	1	5E
2N5194	TO-126	60		60	4	2	100	4	4	2	0.6	1.5	1.2	1.2	1.2	1.5		2	1	5E
2N5195	TO-126	80		80	4	2	100	4	4	2	0.6	1.5	1.2	1.2	1.2	1.5		2	1	5E
2N6107	TO-220	70		75	4	2	100 <sup>†</sup>	6.5	4	2	1.0	6.5	2.0	2.0	2.0	2	250	10	0.5	5E
2N6109	TO-220	50		56	4	2	100 <sup>†</sup>	6.5	4	2	1.0	6.5	2.0	2.0	2.0	2	250	10	0.5	5E
2N6110	TO-220 Lead Form + Clip	30		37.5	4	2	100 <sup>†</sup>	6.5	4	2	1.0	6.5	2.0	2.0	2.0	3	250	10	0.5	5E
2N6111	TO-220	30		37.5	4	2	100 <sup>†</sup>	6.5	4	2	1.0	6.5	2.0	2.0	2.0	3	250	10	0.5	5E
2N6124	TO-220	45		45	4	2	100	4	4	2	0.6	1.5	1.4	1.4	1.5	4		2.5	1	5E
2N6125	TO-220	60		60	4	2	100	4	4	2	0.6	1.5	1.4	1.4	1.5	4		2.5	1	5E
2N6126	TO-220	80		80	4	2	100	4	4	2	0.6	1.5	1.4	1.4	1.5	4		2.5	1	5E
2N6132	TO-220	40		40	7	4	100	7	4	4	1.4	7	7	7	7	7		2.5	1	5E
2N6133	TO-220	60		60	7	4	100	7	4	4	1.4	7	7	7	7	7		2.5	1	5E
2N6134	TO-220	80		60	7	4	100	7	4	4	2.0	7	7	7	7	7		2.5	1	5E
MJE371	TO-220	40			1	1	40	1	1	1										5E
2N4918	TO-126	40		40	1	1	100	1	1	1	0.6	1.3	1.3	1.3	1.3	1	100	3	0.25	5F
2N4919	TO-126	60		60	1	1	100	1	1	1	0.6	1.3	1.3	1.3	1.3	1	100	3	0.25	5F
2N4920	TO-126	80		80	1	1	100	1	1	1	0.6	1.3	1.3	1.3	1.3	1	100	3	0.25	5F

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28C 35462

**POWER (Continued)**

Type No.	Case Style	V <sub>CE0</sub> (V) Min	V <sub>BE0</sub> (V) Min	V <sub>CE0</sub> (V) Min	V <sub>BE0</sub> (V) Min	IC <sub>EX</sub> <sup>+</sup> (μA) Max	V <sub>CB</sub> (V)	hFE Min	hFE Max	IC (A) @ VCE & VBE (V)	V <sub>CE(SAT)</sub> (V) Max	V <sub>BE(SAT)</sub> (V) Min	IC (A) @ VBE(SAT) & VCE(SAT) (V) Min	IC (A) @ VBE(SAT) & VCE(SAT) (V) Max	C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) Min	f <sub>T</sub> (MHz) Max	IC (A) @ VBE(SAT) & VCE(SAT) (V) Min	IC (A) @ VBE(SAT) & VCE(SAT) (V) Max	Process No.
2N6475	TO-220	100		100	100	100	100	15	150	1.5	1.2		1.5	1.5	250	10		0.5	0.5	5F
2N6476	TO-220	120		120	120	100	120	2	150	1.5	1.2		1.5	1.5	250	10		0.5	0.5	5F
MJE370	TO-220	30		30				25	0.2	0.2										5F
TIP30	TO-220	40		40	40	200*	40	15	75	1	0.7		1	1		3		0.2	0.2	5F
TIP30A	TO-220	60		60	60	200*	60	15	75	1	0.7		1	1		3		0.2	0.2	5F
TIP30B	TO-220	80		80	80	200*	80	15	75	1	0.7		1	1		3		0.2	0.2	5F
TIP30C	TO-220	100		100	100	200*	100	15	75	1	0.7		1	1		3		0.2	0.2	5F
TIP32	TO-220	40		40	40	200*	40	10	50	3	1.2		3	3		3		0.5	0.5	5F
TIP32A	TO-220	60		60	60	200*	60	10	50	3	1.2		3	3		3		0.5	0.5	5F
TIP32B	TO-220	80		80	80	200*	80	10	50	3	1.2		3	3		3		0.5	0.5	5F
TIP32C	TO-220	100		100	100	200*	100	10	50	3	1.2		3	3		3		0.5	0.5	5F
TIP62	TO-220	40		40	40	200*	40	15	100	0.5	0.7		0.5	0.5		3		0.05	0.05	5F
TIP62A	TO-220	60		60	60	200*	60	15	100	0.5	0.7		0.5	0.5		3		0.05	0.05	5F
TIP62B	TO-220	80		80	80	200*	80	15	100	0.5	0.7		0.5	0.5		3		0.05	0.05	5F
TIP62C	TO-220	100		100	100	200*	100	15	100	0.5	0.7		0.5	0.5		3		0.05	0.05	5F
D43C1	TO-202 (56)	30		30	30	1 μA	1	10	1A	1A	0.5	1.3	1A	1A	30					5P
D43C2	TO-202 (56)	30		30	30	1 μA	30	20	1A	1A	0.5	1.3	1A	1A	30					5P
D43C3	TO-202 (56)	30		30	30	1 μA	30	20	1A	1A	0.5	1.3	1A	1A	30					5P

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6501130 NATL SEMICOND, (DISCRETE)

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POWER (Continued)

Type No.	Case Style	V <sub>CB0</sub> (V) Min	V <sub>CE0</sub> (V) Min	V <sub>EB0</sub> (V) Min	I <sub>CEX1</sub> <sup>*</sup> (μA) Max	V <sub>CB</sub> (V) @ I <sub>CEX1</sub>	h <sub>FE</sub> Min	h <sub>FE</sub> Max	I <sub>C</sub> (A) @ V <sub>CE</sub>	V <sub>CE(SAT)</sub> (V) Max	V <sub>BE(SAT)</sub> (V) Min	I <sub>C</sub> (A) @ V <sub>BE(SAT)</sub>	C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) Min	f <sub>T</sub> (MHz) Max	I <sub>C</sub> (A)	Process No.
D43C4	TO-202 (56)	45	45		1 μA	45	10	200	1A	0.5	1.3	1A	30				5P
D43C5	TO-202 (56)	45	45		1 μA	45	20	200	1A	0.5	1.3	1A	30				5P
D43C6	TO-202 (56)	45	45		1 μA	45	20	120	2A	0.5	1.3	1A	30				5P
D45C1	TO-220	30	30		10*	40	10	200	1	0.5	1.3	1	125	3	3	0.02	5P
D45C2	TO-220	30	30		10*	40	20	120	0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C3	TO-220	30	30		10*	40	20	40	0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C4	TO-220	45	45		10*	55	10	200	1	0.5	1.3	1	125	3	3	0.02	5P
D45C5	TO-220	45	45		10*	55	20	120	0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C6	TO-220	45	45		10*	55	20	40	0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C7	TO-220	60	60		10*	70	10	200	1	0.5	1.3	1	125	3	3	0.02	5P
D45C8	TO-220	60	60		10*	70	20	120	0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C9	TO-220	60	60		10*	70	20	40	0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C10	TO-220	80	80		10*	90	10	200	1	0.5	1.3	1	125	3	3	0.02	5P
D45C11	TO-220	80	80		10*	90	20	120	0.2	0.5	1.3	1	125	3	3	0.02	5P
D45C12	TO-220	80	80		10*	90	20	40	0.2	0.5	1.3	1	125	3	3	0.02	5P
MJE230	TO-126	40	40				40	200	0.2	0.3	1.8	0.5	70	50	50	0.1	5P
MJE231	TO-126	40	40				40	200	0.2	0.3	1.8	0.5	70	50	50	0.1	5P
MJE232	TO-126	40	40				25	200	0.2	0.3	1.8	0.5	70	50	50	0.1	5P
MJE233	TO-126	60	60				10	200	0.2	0.3	1.8	0.5	70	50	50	0.1	5P

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6501130 NATL SEMICOND, (DISCRETE)

28C 35464

Type No.	Case Style	VCBO (V) Min	VCEO (V) Min	VEBO (V) Min	ICES* (μA) Max	VCE (V) @ IC & VCE	hFE Min	hFE Max	IC (A) @	VCE(SAT) (V) Max	VBE(SAT) (V)		IC (A) @	Cob (pF) Max	fT (MHz) Min	fT (MHz) Max	Process No.
											Min	Max					
MJE234	TO-126		60			0.2 1	150	0.2	0.5	0.3	0.3	1.8	0.1	70	50		5P
MJE235	TO-126		60			0.2 1		1	0.5	0.6	1.8	0.1	70	50		5P	
MJE250	TO-126					0.2 1	200	0.2	0.5	0.3	1.8	0.1	70	40		5P	
MJE251	TO-126		80			0.2 1	120	0.2	0.5	0.8	1.8	0.1	70	40		5P	
MJE252	TO-126		80			0.2 1		1	0.5	0.6	1.8	0.1	70	40		5P	
MJE253	TO-126		100			0.2 1	120	0.2	0.5	0.3	1.8	0.1	70	40		5P	
MJE254	TO-126		100			0.2 1		1	0.5	0.8	1.8	0.1	70	40		5P	
D45H1	TO-220		30			0.2 1	35	2	0.5	1.0	1.5	8					5Q
D45H2	TO-220		30			0.2 1	40	2	0.5	1.0	1.5	8					5Q
D45H4	TO-220		45			0.2 1	20	4	0.5	1.0	1.5	8					5Q
D45H5	TO-220		45			0.2 1	35	2	0.5	1.0	1.5	8					5Q
D45H7	TO-220		60			0.2 1	60	2	0.5	1.0	1.5	8					5Q
D45H8	TO-220		60			0.2 1	40	2	0.5	1.0	1.5	8					5Q
D45H10	TO-220		80			0.2 1	20	4	0.5	1.0	1.5	8					5Q
D45H11	TO-220		80			0.2 1	35	2	0.5	1.0	1.5	8					5Q
MJE210	TO-126		25			0.5 1	70	0.5	0.5	0.3	0.75	2	120	65			5R

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POWER (Continued)

